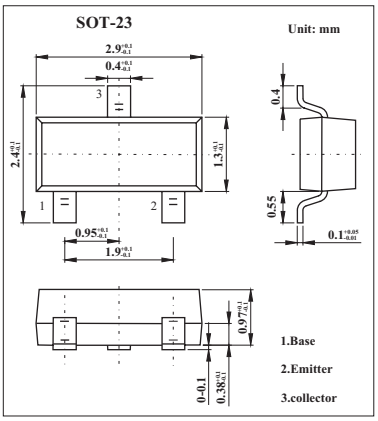
PNP Transistors

KST9015



Features

- Complementary to KST9014

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-45	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current -Continuous	I_C	-0.1	A
Collector Power Dissipation	P_C	0.2	W
Junction Temperature	T_j	150	℃
Storage Temperature	T_{stg}	-55 to 150	℃

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	I_C=-100uA, I_E=0	-50			V
Collector-emitter breakdown voltage	V_{CEO}	I_C=-1mA, I_B=0	-45			V
Emitter-base Breakdown voltage	V_{EBO}	I_E=-100μA, I_C=0	-5			V
Collector cutoff current	I_{CBO}	V_{CB}=-50V, I_E=0			-0.1	μA
Emitter cutoff current	I_{EBO}	V_{EB}=-5V, I_C=0			-0.1	μA
DC current gain	h_{FE}	V_{CE}=-5V, I_C=-1mA	200		1000	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-100mA, I_B=-10mA			-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-100mA, I_B=-10mA			-1	V
Transition frequency	f_T	V_{CE}=-5V, I_C=-10mA,f=30MHZ	150			MHz

h_{FE} Classification

Marking	M6	
Rank	L	H
hFE	200 to 450	450 to 1000

KST9015

■ Typical Characteristics

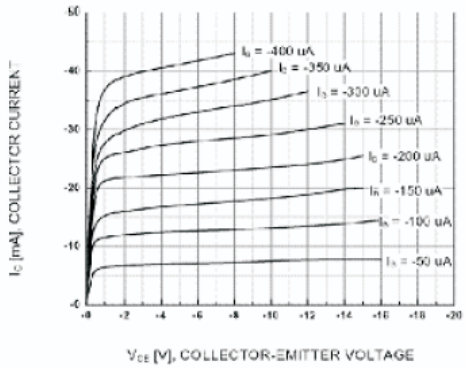


Figure 1. Static Characteristic

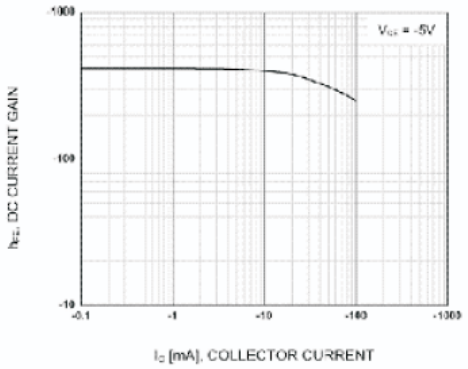


Figure 2. DC current Gain

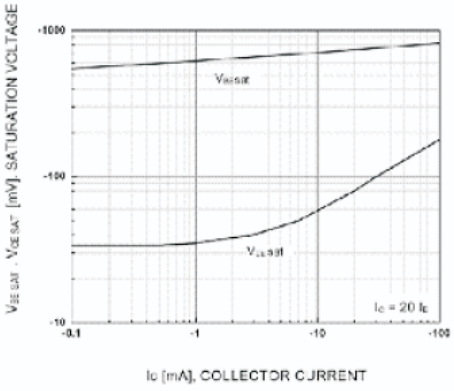


Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

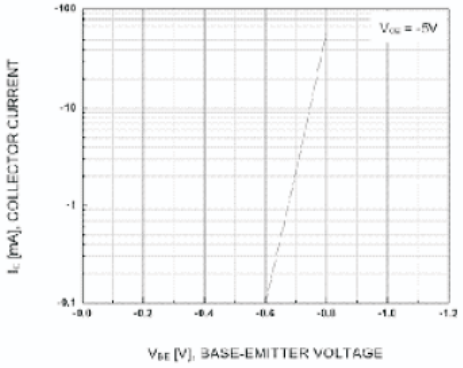


Figure 4. Base-Emitter On Voltage

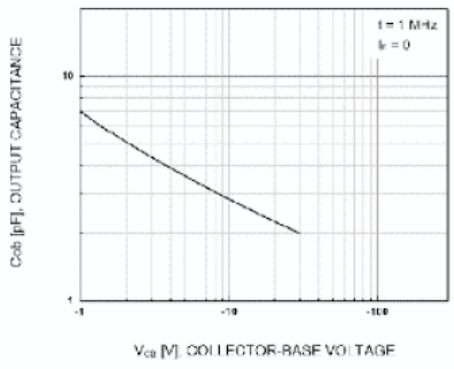


Figure 5. Collector Output Capacitance

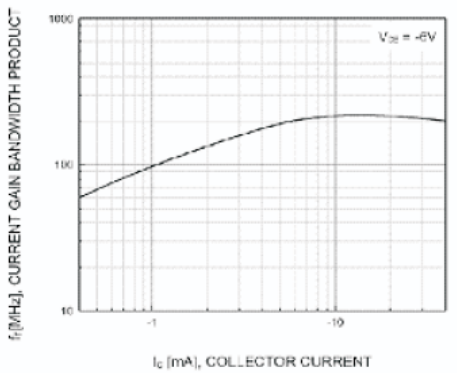


Figure 6. Current Gian Bandwidth Product